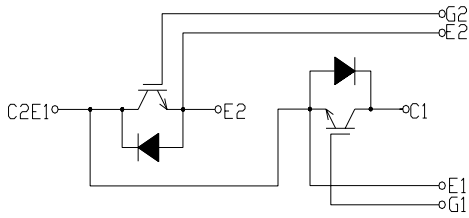
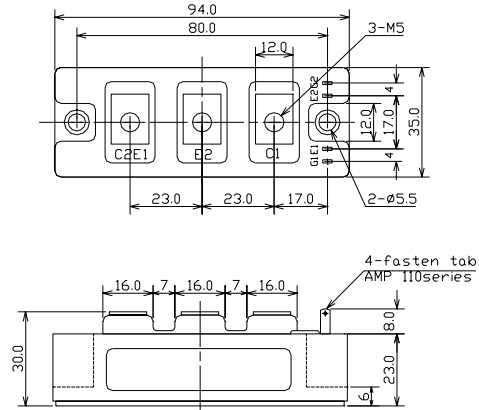


CIRCUIT



OUTLINE DRAWING



4-fasten- tab No 110

Dimension(mm)

Approximate Weight : 220g

MAXMUM RATINGS (Tc=25°C)

Item	Symbol	PDMB100B12C2	Unit
Collector-Emitter Voltage	V _{CEs}	1200	V
Gate - Emitter Voltage	V _{GES}	+/- 20	V
Collector Current	DC	I _C	100
	1 ms	I _C	200
Collector Power Dissipation	P _C	500	W
Junction Temperature Range	T _j	-40 to +150	°C
Storage Temperature Range	T _{sg}	-40 to +125	°C
Isolation Voltage (Terminal to Base AC, 1 min.)	V _{ISO}	2500	V
Mounting Torque	Module Base to Heat sink	F _{TOR}	2.04
	Bus Bar to Main Terminals		
			Nom

ELECTRICAL CHARACTERISTICS (Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Collector-Emitter Cut-Off Current	I _{CEs}	V _{CE} =1200V, V _{GE} =0V	-	-	2.0	mA	
Gate-Emitter Leakage Current	I _{GES}	V _{GE} =+/- 20V, V _{CE} =0V	-	-	1.0	µA	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100A, V _{GE} =15V	-	1.9	2.4	V	
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} =5V, I _C =100mA	4.0	-	8.0	V	
Input Capacitance	C _{ies}	V _{CE} =10V, V _{GE} =0V, f=1MHz	-	8300	-	pF	
Switching Time	Rise Time	t _r	V _{CC} =600V	-	0.25	0.45	µs
	Turn-on Time	t _{on}	R _L =6 ohm	-	0.40	0.7	
	Fall Time	t _f	R _C =10 ohm	-	0.25	0.35	
	Turn-off Time	t _{off}	V _{GE} = +/- 15V	-	0.80	1.10	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

Item	Symbol	Rated Value	Unit
Forward Current	DC	I _F	100
	1 ms	I _{FM}	200
			A

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V _F	I _F =100A, V _{GE} =0V	-	1.9	2.4	V
Reverse Recovery Time	t _{rr}	I _F =100A, V _{CE} =-10V, di/dt=200A/µs	-	0.2	0.3	µs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	R _{th(j-c)}	Junction to Case	-	-	0.24
	DIODE			-	-	0.42
						°C/W

Fig.1- Output Characteristics (Typical)

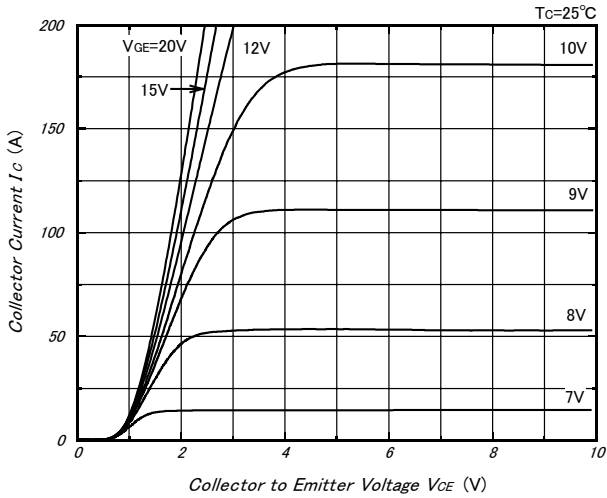


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

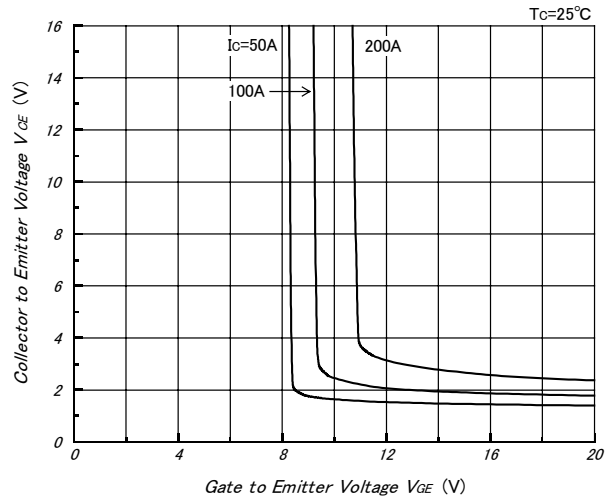


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

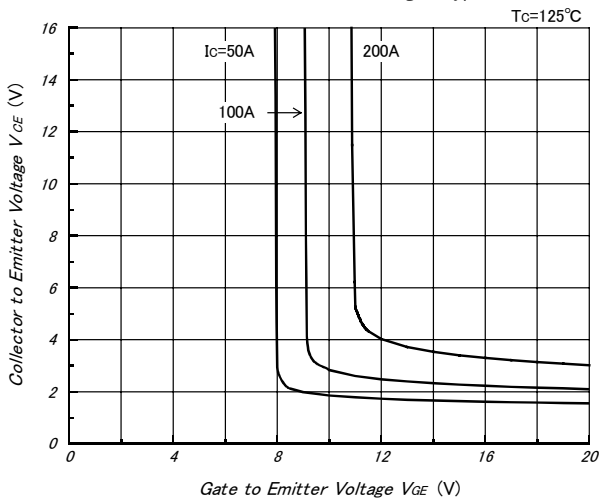


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

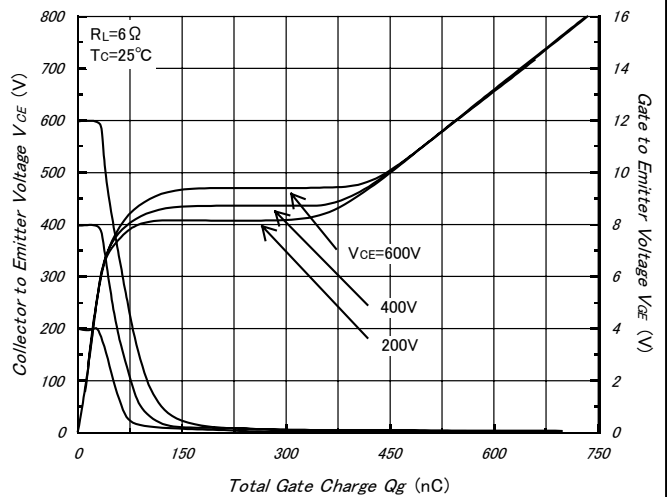


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

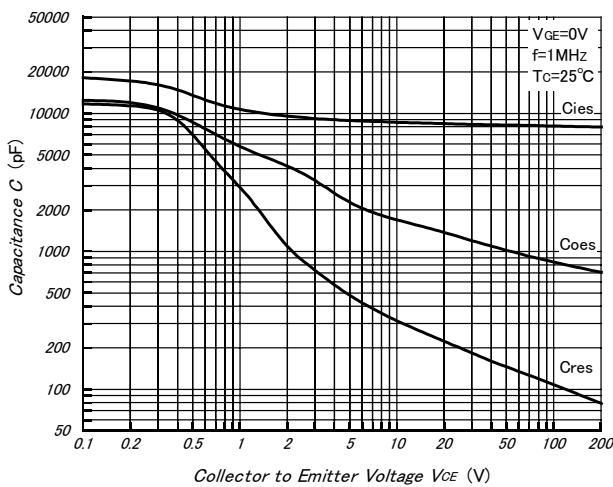


Fig.6- Collector Current vs. Switching Time (Typical)

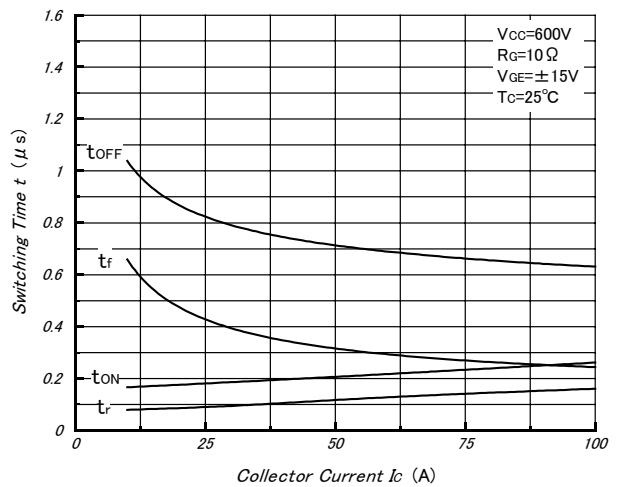


Fig.7- Series Gate Impedance vs. Switching Time (Typical)

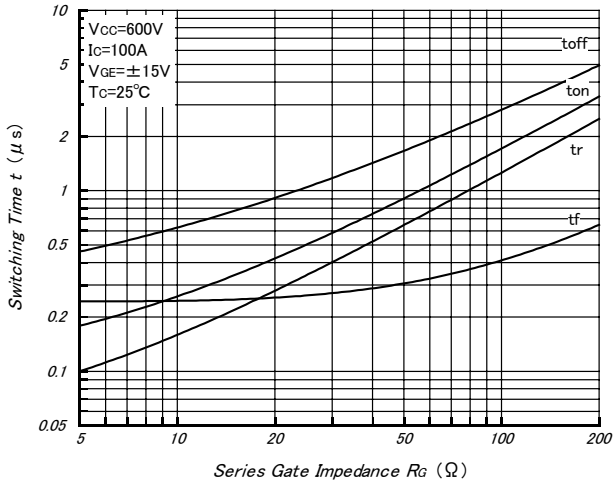


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

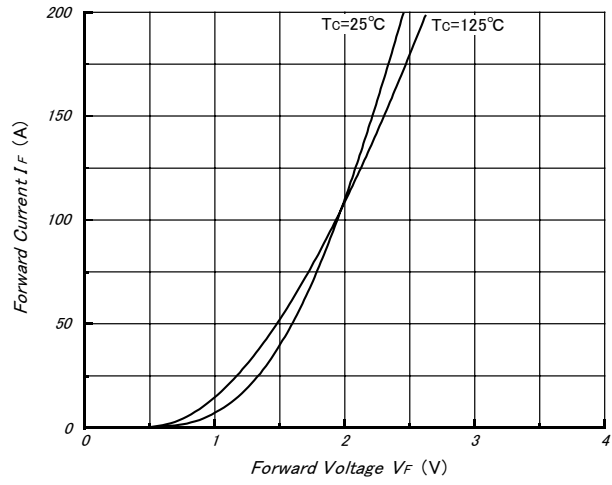


Fig.9- Reverse Recovery Characteristics (Typical)

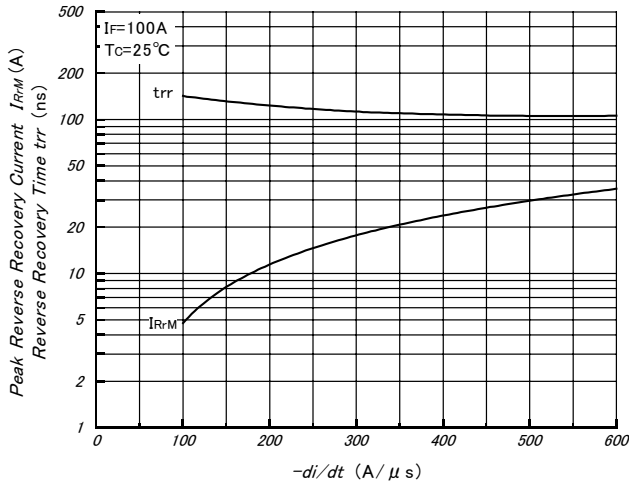


Fig.10- Reverse Bias Safe Operating Area

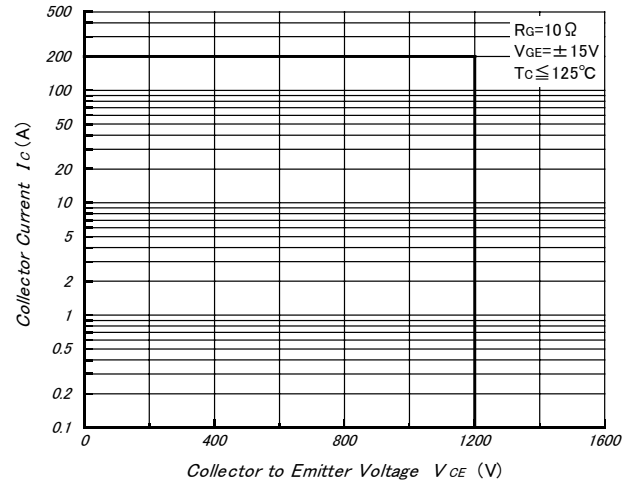


Fig.11- Transient Thermal Impedance

